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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		APPLICANT G. Saito, et al.				
		FILING DATE	EXPECTED GROUP			
		September 10, 2003	2825			

## **U.S. PATENT DOCUMENTS**

Examin Initial	er	Document Number	Date	Name	Class	Subclass	Filing Date
<i>7</i> 61	AA	6,589,879	7/8/2003	Williams, et al.	438	714	15410
IN	AB	4,693,781	9/15/1987	Leung, et al.	156	643	
#1	AC	4,857,477	8/15/1989	Kanamori	437	47	
<i>4</i> 61	AD	6,235,643	5/22/2001	Mui, et al.	438	719	
H1	AE	6,153,494	11/28/2000	Hsieh, et al.	438	424	<u> </u>
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th1	AH	6,432,832	8/13/2002	Miller, et al.	438	7/3	

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						Yes	No
167 AI	2001-345375	12/14/2001	Japan		_	Х	
OTHER DOC	UMENTS (Inclu	uding Autho	r, Title, Date, Pertinent	Pages	, Etc.)		

OTHER	DOC	UMENTS (Inclu	iding Author	r, Title, Date,	Pertinent	Pages	Etc.)	<u> </u>	
The	AJ	UMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) S. Wolf, "Silicon Processing for the VLSI Era", Vol. II, Process Integration, 1990, pages 51-54							
The	AK	TI's "Trench Technology Moves in the Factory", Electronics, July 9, 1987, pages 75-87							
the	AL	R. N. Carlile, et al. "Trench Etches in Silicon with Controllable Sidewall Angles", Electrochem. Soc. Solid-State Science and Technology, August 1988, pages 2058-2064							
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